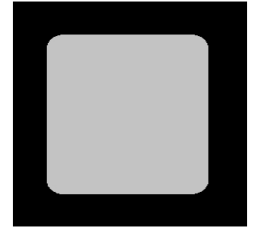


# N3D-0650-004

## Silicon Carbide Schottky Diode Chip



Part Number	Die Size	Anode	Cathode
SIC-0650-004	1.18 x 1.18 mm <sup>2</sup>	Al	Ni/Ag

### Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	650	V		
I <sub>F</sub>	Continuous Forward Current	4.8	A	T <sub>c</sub> =150° C	
V <sub>R</sub>	DC Peak Blocking Voltage	650	V		
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature	-55 to +175	° C		

### Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	Forward Voltage	1.5 1.8	1.8 2.0	V	I <sub>F</sub> = 4 A T <sub>J</sub> = 25°C I <sub>F</sub> = 4 A T <sub>J</sub> = 175°C	Figure 1
I <sub>R</sub>	Reverse Current	1 12	20 100	μA	V <sub>R</sub> = 650 V T <sub>J</sub> = 25°C V <sub>R</sub> = 650 V T <sub>J</sub> = 175°C	Figure 2
Q <sub>C</sub>	Total Capacitive Charge	9.5		nC	V <sub>R</sub> = 400 V, T <sub>J</sub> = 25°C Q <sub>C</sub> = ∫ <sub>0</sub> <sup>V<sub>R</sub></sup> C(V)dV	Figure 4
C	Total Capacitance	185 19.0 16.7		pF	V <sub>R</sub> = 0 V, T <sub>J</sub> = 25°C, f = 1 MHz V <sub>R</sub> = 200 V, T <sub>J</sub> = 25°C, f = 1 MHz V <sub>R</sub> = 400 V, T <sub>J</sub> = 25°C, f = 1 MHz	Figure 3
E <sub>c</sub>	Capacitance Stored Energy	2.4		μJ	V <sub>R</sub> = 400 V	

### Mechanical Parameters

Parameter	Typ.	Unit
Die Size	1.18 x 1.18	mm
Anode Pad Size	0.92 x 0.92	mm
Anode Pad Opening	0.70 x 0.70	mm
Thickness	180 ± 10%	μ m
Wafer Size	100	mm
Anode Metalization (Al)	4	μ m
Cathode Metalization (Ni/Ag)	1.5	μ m
Frontside Passivation	Polyimide	

## Typical Performance

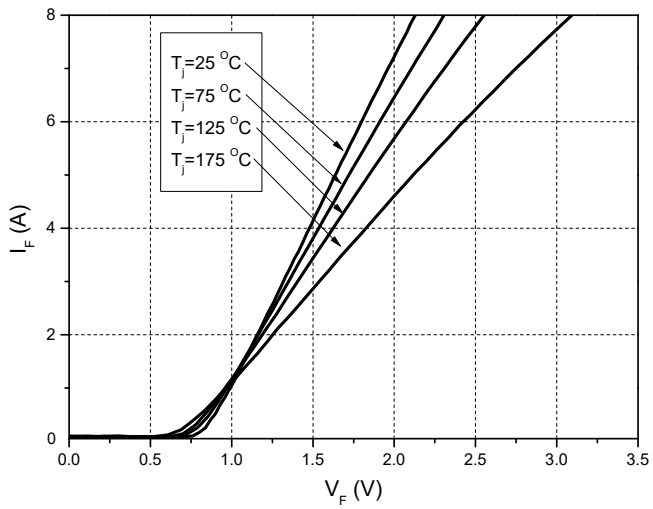


Figure 1. Forward Characteristics

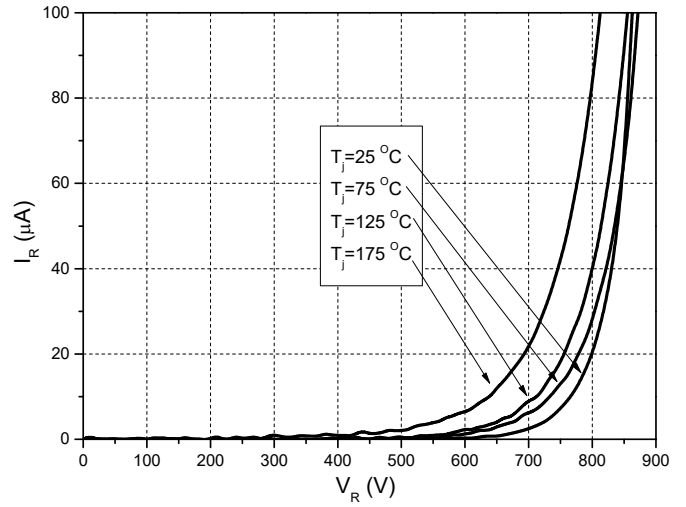


Figure 2. Reverse Characteristics

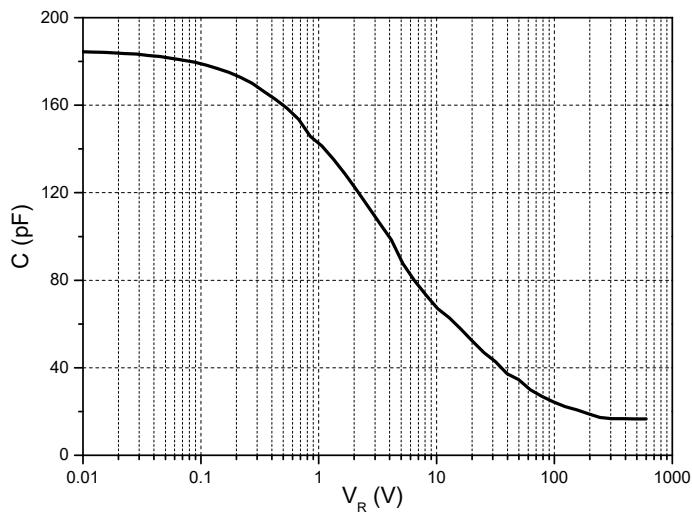


Figure 3. Capacitance vs. Reverse Voltage

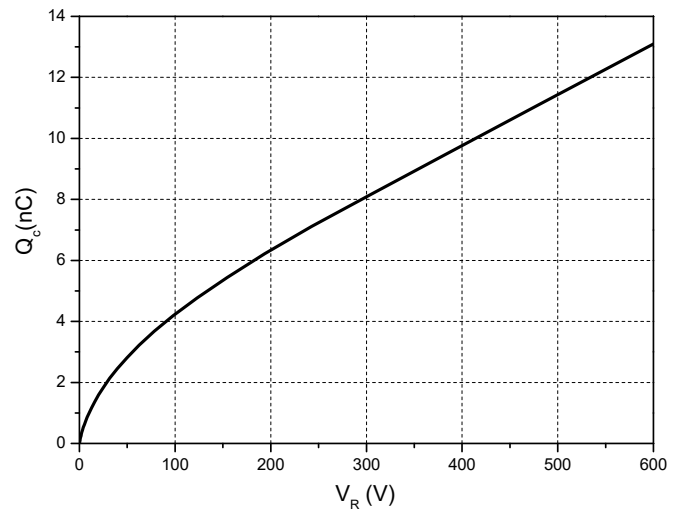
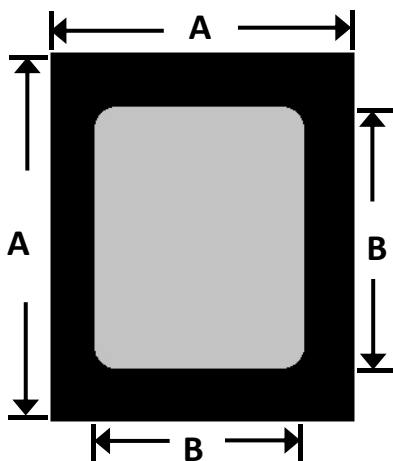


Figure 4. Total Capacitance Charge vs. Reverse Voltage

## Chip Dimensions



Symbol	Dimension(mm)
A	1.18
B	0.70